



45V NPN HIGH GAIN MEDIUM POWER TRANSISTOR

Features

- BV_{CEO} > 45V
- I_C = 3A High Continuous Collector Current
- I_{CM} = 6A Peak Pulse Current
- High Gain Device >400 @1A
- R_{CE(SAT)} = 77mΩ for Low Equivalent On-Resistance
- hFE Specified Up to 6A for a High Gain Hold Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

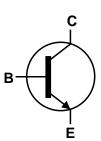
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.34 grams (Approximate)

Applications

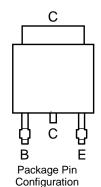
- DC-DC Converters
- Power Switches
- IGBT & MOSFET Gate Drivers
- Motor Control
- Automotive Circuits
- Siren Drivers



Top View



Equivalent Circuit



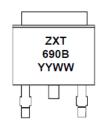
Ordering Information (Note 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXT690BKTC	AEC-Q101	ZXT690B	13	16	2,500
ZXT690BKQTC	Automotive	ZXT690B	13	16	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



ZXT690B = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 17 = 2017) WW = Week Code (01 - 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	BV _{CBO}	60	V
Collector-Emitter Voltage	BV _{CEO}	45	V
Emitter-Base Voltage	BV _{EBO}	7	V
Continuous Collector Current	Ic	3	Α
Peak Pulse Current	I _{CM}	6	Α
Base Current	I _B	0.5	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		4.0		
Power Dissipation	(Note 7)	P _D	3.4	W	
Power Dissipation	(Note 8)		2.1	VV	
	(Note 9)		1.6		
	(Note 6)		32		
Thermal Decistance, Junction to Ambient Air	(Note 7)	R _θ ЈА	36		
Thermal Resistance, Junction to Ambient Air	(Note 8)		59	2011	
	(Note 9)		80	°C/W	
Thermal Resistance, Junction to Leads	(Note 10)	$R_{ heta JL}$	3		
Thermal Resistance, Junction to Case	(Note 11)	R ₀ JC	14.6		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 12)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

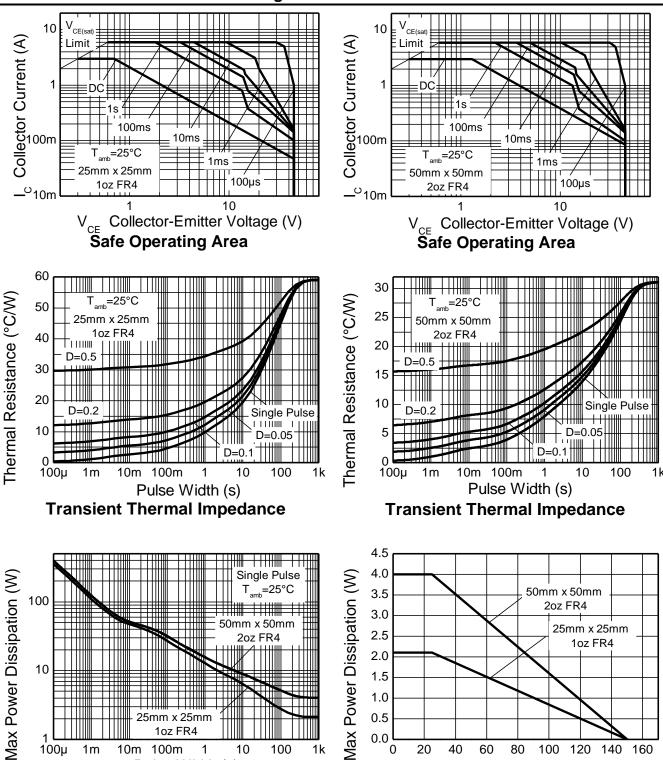
- 6. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured For a device mounted with the exposed collector pad on 50mm x 50mm 2oz coppe under still air conditions whilst operating in a steady-state.
 Same as Note (6), except mounted on 25mm x 25mm 2oz copper.
 Same as Note (6), except mounted on 25mm x 25mm 1oz copper.
 Same as Note (6), except mounted on minimum recommended pad (MRP) layout.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Thermal resistance from junction to the top of the case.
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information

Pulse Width (s)

Pulse Power Dissipation



Temperature (°C)

Derating Curve



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

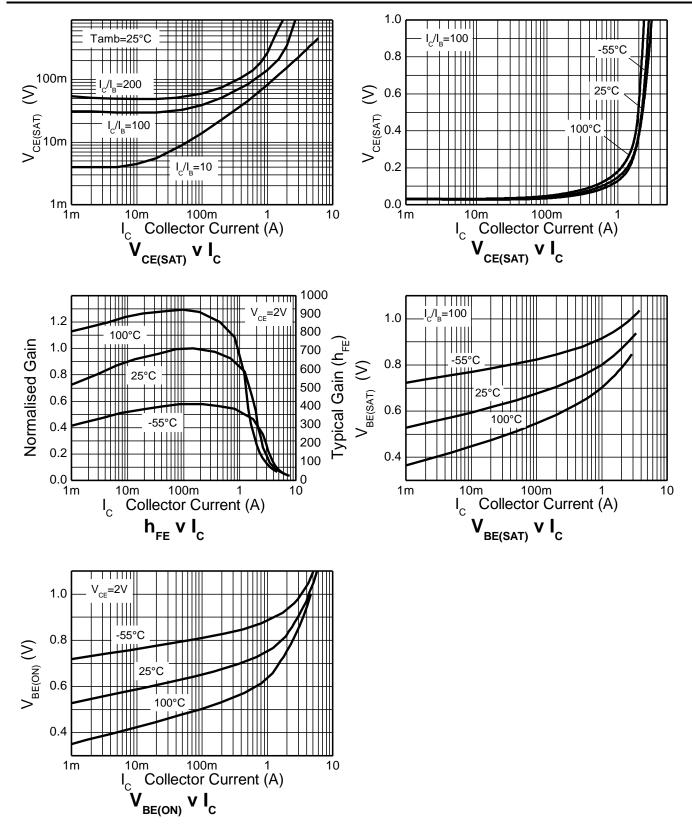
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	60	145		V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 13)	BV_{CEO}	45	65	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.2	_	V	$I_E = 100\mu A$
Collector Cutoff Current	I _{CBO}	_	<1	20	nA	V _{CB} = 35V
Collector Cutoff Current	ICES	_	<1	20	nA	V _{CE} = 35V
Emitter Cutoff Current	I _{EBO}	_	<1	20	nA	V _{EB} = 5.6V
			50	85	mV	$I_C = 0.1A$, $I_B = 0.5mA$
Collector Emitter Seturation Voltage (Note 42)	V _{CE(SAT)}	_	240	360		I _C = 1A, I _B = 5mA
Collector-Emitter Saturation Voltage (Note 13)			210	320		I _C = 2A, I _B = 40mA
			230	350		I _C = 3A, I _B = 150mA
Base-Emitter Saturation Voltage (Note 13)	V _{BE(SAT)}	_	1.0	1.2	V	I _C = 3A, I _B = 150mA
Base-Emitter Turn-On Voltage (Note 13)	$V_{BE(ON)}$	_	0.9	1.1	V	$I_C = 3A$, $V_{CE} = 2V$
	h _{FE}	500	700			I _C = 100mA, V _{CE} = 2V
DC Current Coin (Note 12)		400	600			I _C = 1A, V _{CE} = 2V
DC Current Gain (Note 13)		150	350		_	I _C = 2A, V _{CE} = 2V
		60	120			$I_C = 3A$, $V_{CE} = 2V$
Current Gain-Bandwidth Product	f _T	150	_	_	MHz	$I_C = 50 \text{mA}, V_{CE} = 5 \text{V}, f = 50 \text{MHz}$
Output Capacitance	C _{OBO}	_	16	_	pF	V _{CB} = 10V, f = 1MHz
Turn-On Time	t _{ON}	_	33	_	ns	I _C = 500mA, V _{CC} = 10V,
Turn-Off Time	t _{OFF}	_	1,300	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

Note: 13. Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%.

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Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

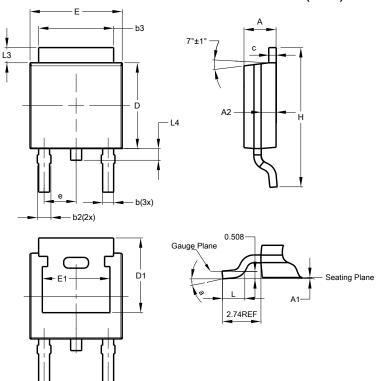




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

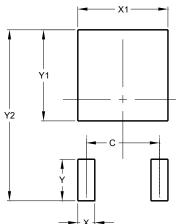


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Ε	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
٦	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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